

# XN04321

Silicon NPN epitaxial planar transistor (Tr1)  
 Silicon PNP epitaxial planar transistor (Tr2)

For switching/digital circuits

■ Features

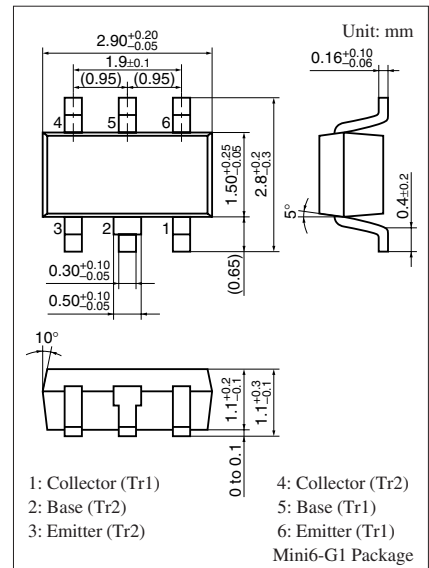
- Two elements incorporated into one package  
 (Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

■ Basic Part Number of Element

- UNR2221 (UN2221) + UNR2121 (UN2121)

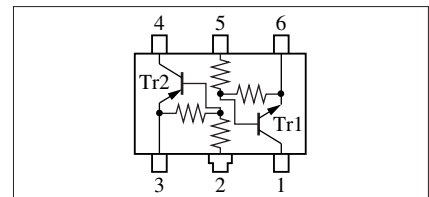
■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	$V_{CBO}$	50 V
	Collector-emitter voltage (Base open)	$V_{CEO}$	50 V
	Collector current	$I_C$	500 mA
Tr2	Collector-base voltage (Emitter open)	$V_{CBO}$	-50 V
	Collector-emitter voltage (Base open)	$V_{CEO}$	-50 V
	Collector current	$I_C$	-500 mA
Overall	Total power dissipation	$P_T$	300 mW
	Junction temperature	$T_j$	150 $^\circ\text{C}$
	Storage temperature	$T_{stg}$	-55 to +150 $^\circ\text{C}$



Marking Symbol: EB

Internal Connection



■ Electrical Characteristics  $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

- Tr1

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 10 \mu\text{A}, I_E = 0$	50			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 2 \text{ mA}, I_B = 0$	50			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 50 \text{ V}, I_E = 0$			1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 50 \text{ V}, I_B = 0$			1	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 6 \text{ V}, I_C = 0$			5	mA
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 10 \text{ V}, I_C = 100 \text{ mA}$	40			—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100 \text{ mA}, I_B = 5 \text{ mA}$			0.25	V
Output voltage high level	$V_{OH}$	$V_{CC} = 5 \text{ V}, V_B = 0.5 \text{ V}, R_L = 500 \Omega$	4.9			V
Output voltage low level	$V_{OL}$	$V_{CC} = 5 \text{ V}, V_B = 3.5 \text{ V}, R_L = 500 \Omega$			0.2	V
Input resistance	$R_1$		-30%	2.2	+30%	k $\Omega$
Resistance ratio	$R_1 / R_2$		0.8	1.0	1.2	—
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

Note) The part number in the parenthesis shows conventional part number.

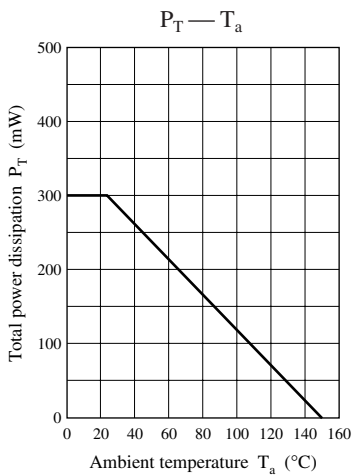
■ Electrical Characteristics (continued)  $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

• Tr2

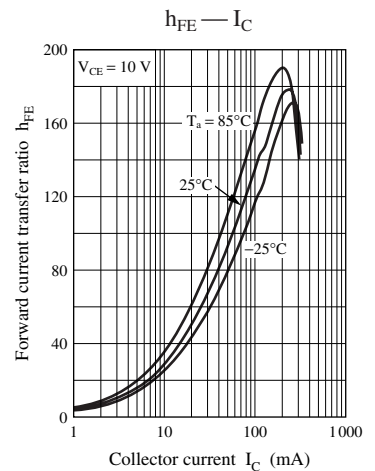
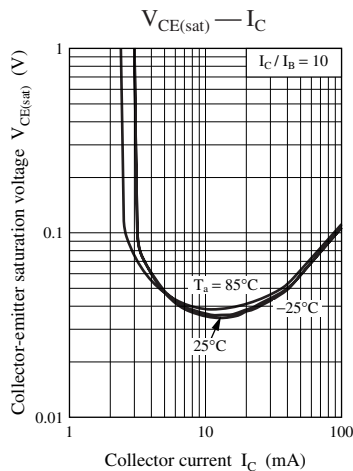
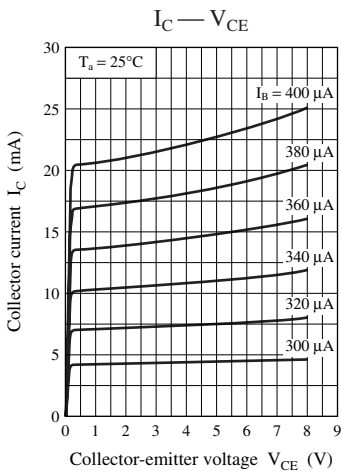
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = -10 \mu\text{A}, I_E = 0$	-50			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = -2 \text{ mA}, I_B = 0$	-50			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -50 \text{ V}, I_E = 0$			-1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = -50 \text{ V}, I_B = 0$			-1	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = -6 \text{ V}, I_C = 0$			-5	mA
Forward current transfer ratio	$h_{FE}$	$V_{CE} = -10 \text{ V}, I_C = -100 \text{ mA}$	40			—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100 \text{ mA}, I_B = -5 \text{ mA}$			-0.25	V
Output voltage high level	$V_{OH}$	$V_{CC} = -5 \text{ V}, V_B = -0.5 \text{ V}, R_L = 500 \Omega$	-4.9			V
Output voltage low level	$V_{OL}$	$V_{CC} = -5 \text{ V}, V_B = -3.5 \text{ V}, R_L = 500 \Omega$			-0.2	V
Input resistance	$R_1$		-30%	2.2	+30%	k $\Omega$
Resistance ratio	$R_1 / R_2$		0.8	1.0	1.2	—
Transition frequency	$f_T$	$V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz

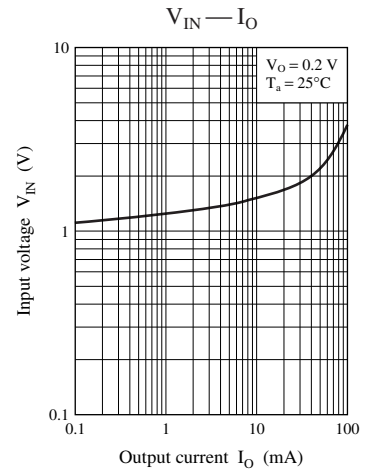
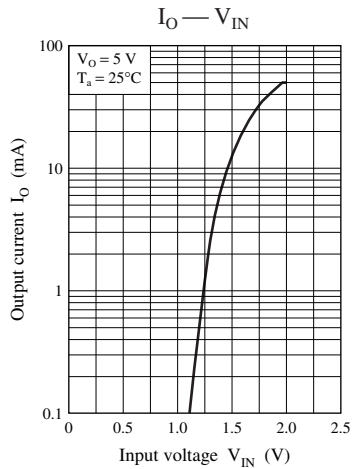
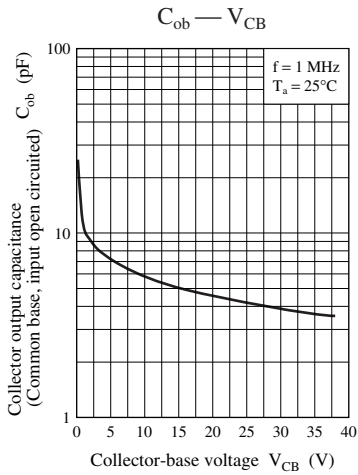
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

Common characteristics chart

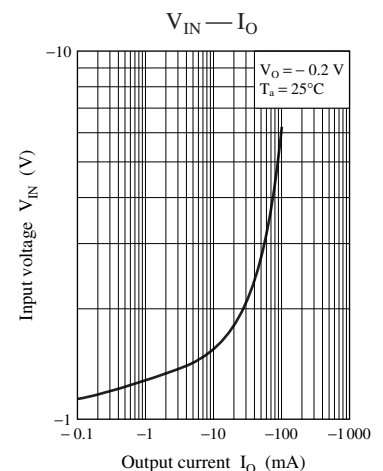
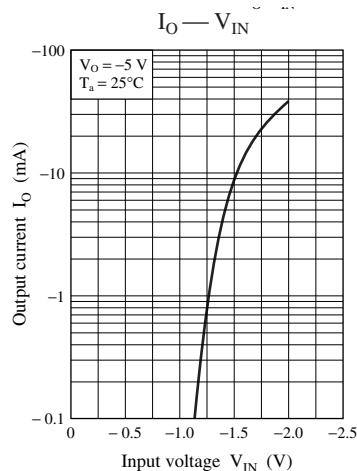
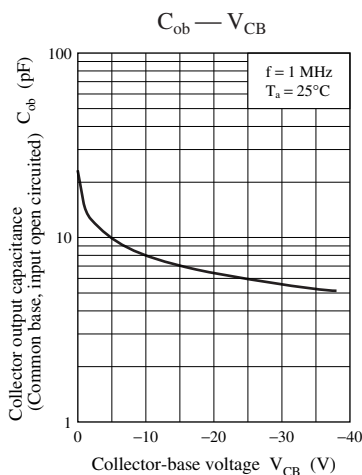
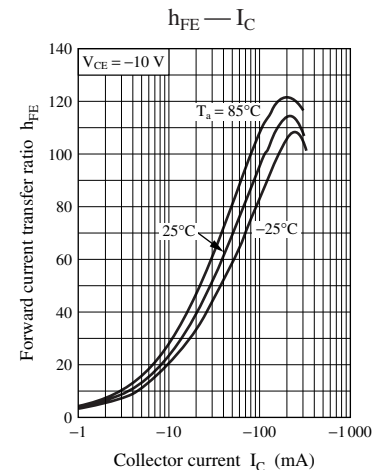
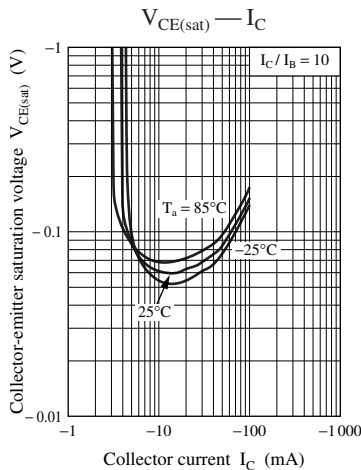
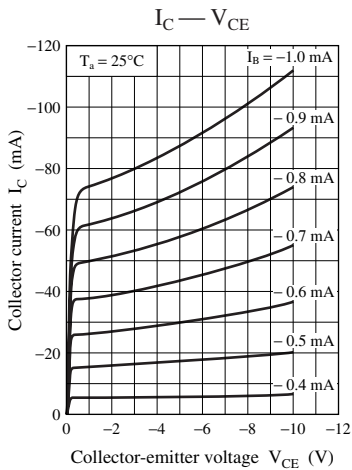


Characteristics charts of Tr1





Characteristics charts of Tr2



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